**TENTATIVE** 

TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

## 800JXH23

## HIGH SPEED RECTIFIER APPLICATIONS

Repetitive Peak Reverse Voltage : V<sub>RRM</sub>=6000V

Average Forward Current : IF(AV)=800A

• Double Side Cooling

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	6000	V
$\label{eq:non-Repetitive Peak Reverse} $$ Voltage (Non-Repetitive $\le 5 ms, $$ T_j $\le 0 $\sim 125 ^{\circ}C)$ $$$	V <sub>RSM</sub>	6300	V
Average Forward Current	I <sub>F (AV)</sub>	800	Α
Peak One Cycle Surge Forward Current (Non-Repetitive, 10ms Width Half Sine Waveform)	I <sub>FSM</sub>	16000	A
Junction Temperature Range	Tj	-40~125	°C
Storage Temperature Range	$T_{ m stg}$	-40~150	°C
Mounting Force	_	29.4±9.8	kN

Unit in mm

2 - \$\tilde{g}\_{3.5 \pm 0.2}\$

DEPTH 2.1 \pm 0.4

\$\tilde{g}\_{60 \pm 0.5}\$

\$\tilde{g}\_{93 \text{MAX}}\$

2 - \$\tilde{g}\_{3.5 \pm 0.2}\$

Creepage path
\$\tilde{g}\_{35 \text{mm}}\$

2 - \$\tilde{g}\_{3.5 \pm 0.2}\$

Creepage path
\$\tilde{g}\_{35 \text{mm}}\$

1. CATHODE
2. ANODE

JEDEC —

EIAJ —

TOSHIBA 3-93B1A

Weight: 800g

## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Reverse Current	$I_{RRM}$	V <sub>RRM</sub> =6000V, T <sub>j</sub> =125°C	_	_	100	mA
Peak Forward Voltage	$V_{\mathbf{FM}}$	$I_{FM} = 2500A, T_j = 125$ °C	_	5.0	_	V
Reverse Recovery Charge	$Q_{rr}$	$I_{F}$ =800A, $T_{j}$ =125°C $di_{F}/dt$ =100A/ $\mu$ s	_	1800	_	$\mu$ C
Thermal Resistance	R <sub>th (j-f)</sub>	DC	<u> </u>	_	0.014	°C/W

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